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(54) **POLISHING COMPOSITION FOR SEMICONDUCTOR WAFER, METHOD FOR PRODUCTION THEREOF AND POLISHING METHOD**

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(58) **Field of Classification Search** 51/307–309; 106/3; 438/691–694

See application file for complete search history.

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(57) **ABSTRACT**

The present invention relates to a polishing composition for a substrate including a metal such as wiring, etc., formed on a semiconductor wafer, which can provide a high polishing rate without causing scratches on the wiring metal, a method of producing the polishing composition, and a polishing method. The polishing composition for a semiconductor wafer comprises an acid and an aqueous medium dispersion containing positively-charged silica particles having an amino group-containing silane coupling agent bonded on a surface thereof, the polishing composition having a pH of 2 to 6.

7 Claims, No Drawings